

# Shottky barrier diode

## RB715W

### ●Application

Low current rectification

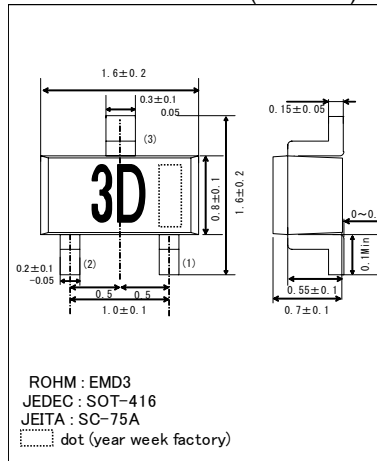
### ●Features

- 1) Ultra small mold type. (EMD3)
- 2) Low  $V_F$
- 3) High reliability.

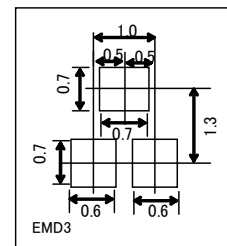
### ●Construction

Silicon epitaxial planer

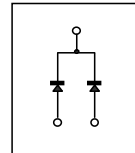
### ●External dimensions (Unit : mm)



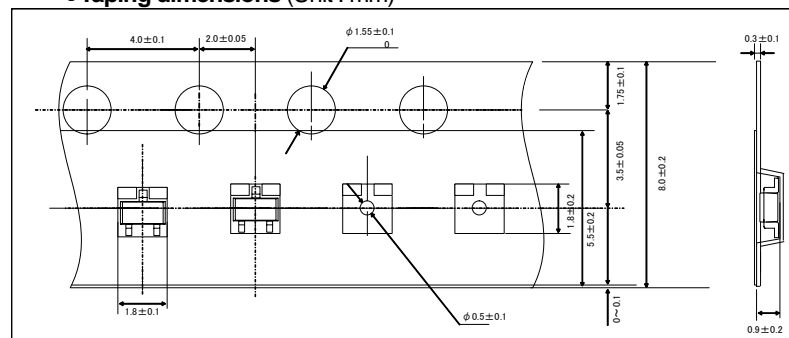
### ●Lead size figure (Unit : mm)



### ●Structure



### ●Taping dimensions (Unit : mm)



### ●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	$V_{RM}$	40	V
Reverse voltage (DC)	$V_R$	40	V
Average rectified forward current	$I_o$	30	mA
Forward current surge peak (60Hz · 1cyc) (*1)	$I_{FSM}$	200	mA
Junction temperature	$T_j$	125	°C
Storage temperature	$T_{stg}$	-40 to +125	°C

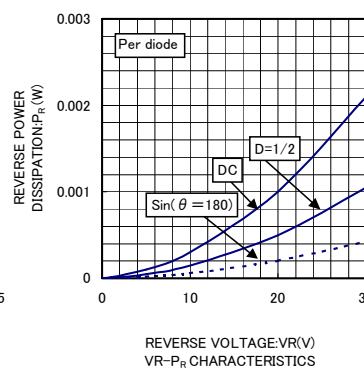
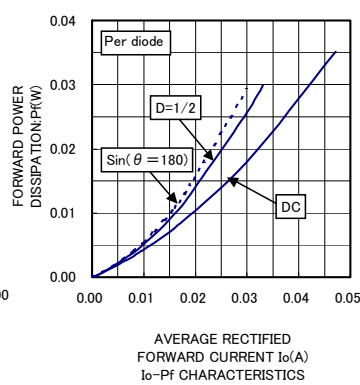
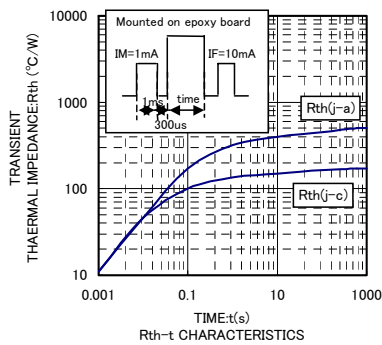
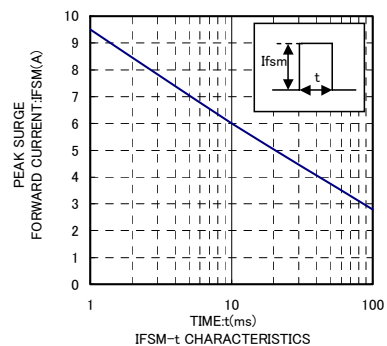
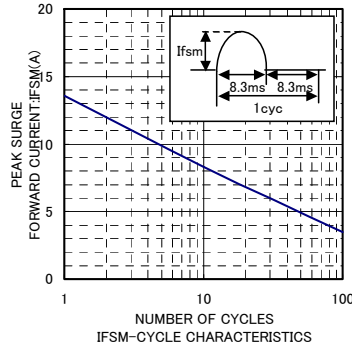
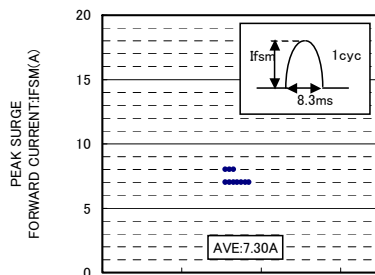
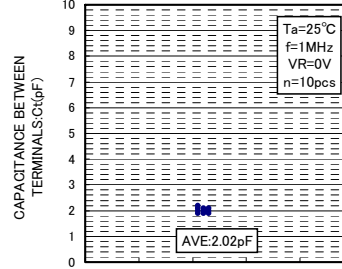
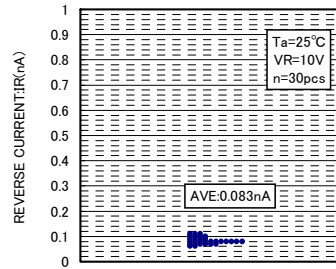
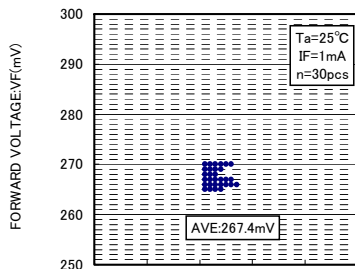
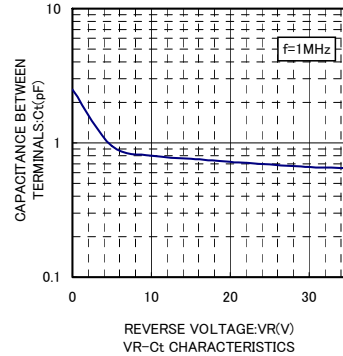
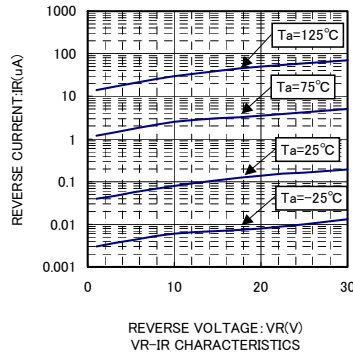
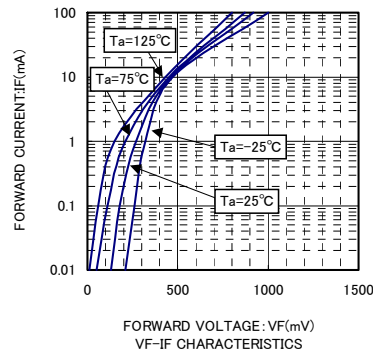
(\*1)Rating of per diode

### ●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	$V_F$	-	-	0.37	V	$I_F=1mA$
Reverse current	$I_R$	-	-	1	$\mu A$	$V_R=10V$
Capacitance between terminals	$C_t$	-	2.0	-	pF	$V_R=1.0V$ $f=1.0MHz$

Diodes

●Electrical characteristic curves (Ta=25°C)



Diodes

